

Low Offset Voltage Dual Comparators

LM393, LM393E, LM293, LM2903, LM2903E, LM2903V, NCV2903

The LM393 series are dual independent precision voltage comparators capable of single or split supply operation. These devices are designed to permit a common mode range—to—ground level with single supply operation. Input offset voltage specifications as low as 2.0 mV make this device an excellent selection for many applications in consumer, automotive, and industrial electronics.

Features

- Wide Single-Supply Range: 2.0 Vdc to 36 Vdc
- Split–Supply Range: ±1.0 Vdc to ±18 Vdc
- Very Low Current Drain Independent of Supply Voltage: 0.4 mA
- Low Input Bias Current: 25 nA
- Low Input Offset Current: 5.0 nA
- Low Input Offset Voltage: 5.0 mV (max) LM293/393
- Input Common Mode Range to Ground Level
- Differential Input Voltage Range Equal to Power Supply Voltage
- Output Voltage Compatible with DTL, ECL, TTL, MOS, and CMOS Logic Levels
- ESD Clamps on the Inputs Increase the Ruggedness of the Device without Affecting Performance
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

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PDIP-8 N SUFFIX CASE 626

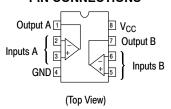


SOIC-8 D SUFFIX CASE 751



Micro8™ DM SUFFIX CASE 846A

PIN CONNECTIONS



DEVICE MARKING AND ORDERING INFORMATION

See detailed marking information and ordering and shipping information on page 7 of this data sheet.

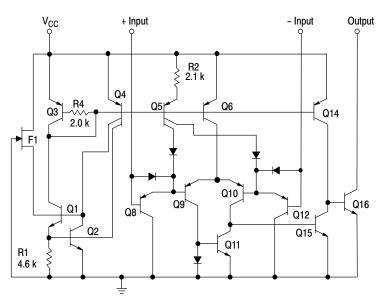


Figure 1. Representative Schematic Diagram

(Diagram shown is for 1 comparator)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Power Supply Voltage	V _{CC}	+36 or ±18	V
Input Differential Voltage	V_{IDR}	36	V
Input Common Mode Voltage Range	V_{ICR}	-0.3 to +36	V
Output Voltage	Vo	36	V
Output Short Circuit-to-Ground Output Sink Current (Note 1)	I _{SC}	Continuous 20	mA
Power Dissipation @ T _A = 25°C Derate above 25°C	P _D 1/R _{θJA}	570 5.7	mW mW/°C
Operating Ambient Temperature Range LM293 LM393, LM393E LM2903, LM2903E LM2903V, NCV2903 (Note 2)	T _A	-25 to +85 0 to +70 -40 to +105 -40 to +125	°C
Maximum Operating Junction Temperature LM393, LM393E, LM2903, LM2903E, LM2903V LM293, NCV2903	T _{J(max)}	150 150	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ESD RATINGS

Rating	НВМ	ММ	Unit
ESD Protection at any Pin (Human Body Model – HBM, Machine Model – MM)			
NCV2903 (Note 2)	2000	200	V
LM393E, LM2903E	1500	150	V
LM393DG/DR2G, LM2903DG/DR2G	250	100	V
All Other Devices	1500	150	V

The maximum output current may be as high as 20 mA, independent of the magnitude of V_{CC}, output short circuits to V_{CC} can cause excessive heating and eventual destruction.
 NCV2903 is qualified for automotive use.

ELECTRICAL CHARACTERISTICS ($V_{CC} = 5.0 \text{ Vdc}$, $T_{low} \le T_A \le T_{high}$, unless otherwise noted.)

		LM29	93, LM39	3, LM393E		LM2903, NCV29	' ' '	
Characteristic	Symbol	Min	Тур	Max	Min	Тур	Max	Unit
Input Offset Voltage (Note 4)	V _{IO}							mV
$T_A = 25$ °C		-	±1.0	±5.0	_	±2.0	±7.0	
$T_{low} \le T_A \le T_{high}$		-	_	±9.0	_	±9.0	±15	
Input Offset Current	I _{IO}							nA
$T_A = 25^{\circ}C$		_	±5.0	±50	_	±5.0	±50	
$T_{low} \le T_A \le T_{high}$		-	_	±150	_	±50	±200	
Input Bias Current (Note 5)	I _{IB}							nA
$T_A = 25^{\circ}C$		_	20	250	_	20	250	
$T_{low} \le T_A \le T_{high}$		_	_	400	_	20	500	
Input Common Mode Voltage Range (Note 6)	V_{ICR}							V
$T_A = 25^{\circ}C$		0	_	V _{CC} -1.5	0	-	V _{CC} -1.5	
$T_{low} \le T_A \le T_{high}$		0	_	V _{CC} -2.0	0	_	V _{CC} -2.0	
Voltage Gain	A _{VOL}	50	200	-	25	200	-	V/mV
$R_L \ge 15 \text{ k}\Omega$, $V_{CC} = 15 \text{ Vdc}$, $T_A = 25^{\circ}C$								
Large Signal Response Time	-	-	300	-	_	300	-	ns
V _{in} = TTL Logic Swing, V _{ref} = 1.4 Vdc								
V_{RL} = 5.0 Vdc, R_L = 5.1 k Ω , T_A = 25°C								
Response Time (Note 7)	t _{TLH}	_	1.3	_	_	1.5	-	μS
V_{RL} = 5.0 Vdc, R_L = 5.1 k Ω , T_A = 25°C								
Input Differential Voltage (Note 8)	V_{ID}	-	_	V _{CC}	_	_	V _{CC}	V
All V _{in} ≥ GND or V− Supply (if used)								
Output Sink Current	I _{Sink}	6.0	16	_	6.0	16	_	mA
$V_{in} \ge 1.0 \text{ Vdc}, V_{in+} = 0 \text{ Vdc}, V_{O} \le 1.5 \text{ Vdc } T_{A} = 25^{\circ}\text{C}$	Ollik							
Output Saturation Voltage	V _{OL}							mV
$V_{in} \ge 1.0 \text{ Vdc}, V_{in+} = 0, I_{Sink} \le 4.0 \text{ mA}, T_A = 25^{\circ}\text{C}$	I OL	_	150	400	_	_	400	
$T_{low} \le T_A \le T_{high}$		-	_	700	_	200	700	
Output Leakage Current	l _{OL}			<u> </u>				nA
$V_{in-} = 0 \text{ V, } V_{in+} \ge 1.0 \text{ Vdc, } V_O = 5.0 \text{ Vdc, } T_A = 25^{\circ}\text{C}$		_	0.1	_	_	0.1	_	
$V_{in-} = 0 \text{ V}, V_{in+} \ge 1.0 \text{ Vdc}, V_{O} = 30 \text{ Vdc},$								
$T_{low} \le T_A \le T_{high}$		-	_	1000	_	-	1000	
Supply Current	I _{CC}							mA
$R_L = \infty$ Both Comparators, $T_A = 25^{\circ}$ C		_	0.4	1.0	_	0.4	1.0	
R _L = ∞ Both Comparators, V _{CC} = 30 V		_	_	2.5	-	_	2.5	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

LM293 T_{low} = -25°C, T_{high} = +85°C LM393, LM393E T_{low} = 0°C, T_{high} = +70°C LM2903, LM2903E T_{low} = -40°C, T_{high} = +105°C LM2903V & NCV2903 T_{low} = -40°C, T_{high} = +125°C

NCV2903 is qualified for automotive use.

- 3. The maximum output current may be as high as 20 mA, independent of the magnitude of V_{CC} , output short circuits to V_{CC} can cause excessive heating and eventual destruction.
- 4. At output switch point, $V_O \simeq 1.4$ Vdc, $R_S = 0~\Omega$ with V_{CC} from 5.0 Vdc to 30 Vdc, and over the full input common mode range (0 V to $V_{CC} = -1.5 \text{ V}$).
- 5. Due to the PNP transistor inputs, bias current will flow out of the inputs. This current is essentially constant, independent of the output state, therefore, no loading changes will exist on the input lines.
- 6. Input common mode of either input should not be permitted to go more than 0.3 V negative of ground or minus supply. The upper limit of common mode range is V_{CC} –1.5 V.
- 7. Response time is specified with a 100 mV step and 5.0 mV of overdrive. With larger magnitudes of overdrive faster response times are obtainable.
- 8. The comparator will exhibit proper output state if one of the inputs becomes greater than V_{CC}, the other input must remain within the common mode range. The low input state must not be less than -0.3 V of ground or minus supply.

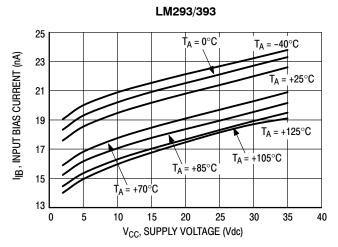


Figure 2. Input Bias Current versus Power Supply Voltage

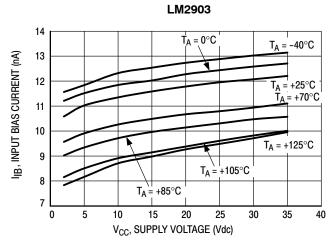


Figure 3. Input Bias Current versus Power Supply Voltage

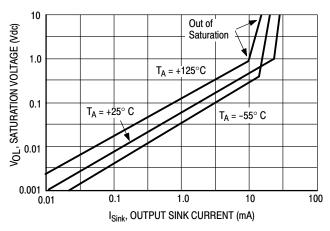


Figure 4. Output Saturation Voltage versus Output Sink Current

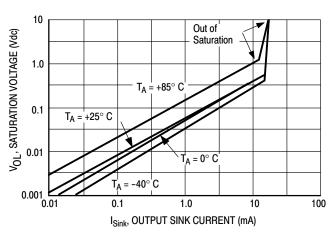


Figure 5. Output Saturation Voltage versus Output Sink Current

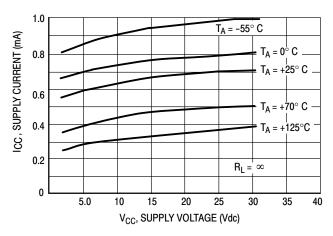


Figure 6. Power Supply Current versus Power Supply Voltage

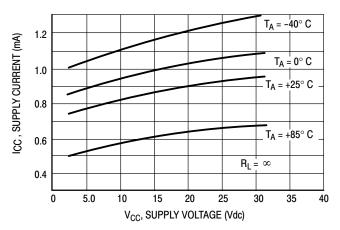
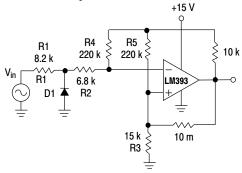


Figure 7. Power Supply Current versus Power Supply Voltage

APPLICATIONS INFORMATION

These dual comparators feature high gain, wide bandwidth characteristics. This gives the device oscillation tendencies if the outputs are capacitively coupled to the inputs via stray capacitance. This oscillation manifests itself during output transitions (V_{OL} to V_{OH}). To alleviate this situation, input resistors < 10 k Ω should be used.



D1 prevents input from going negative by more than 0.6 $\rm V.$

$$R1 + R2 = R3$$

$$R3 \le \frac{R5}{12}$$
 for small error in zero crossing.

Figure 8. Zero Crossing Detector (Single Supply)

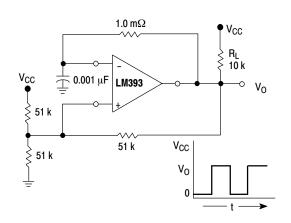
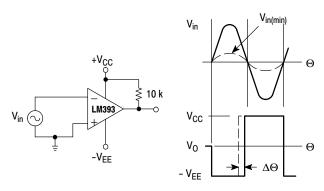


Figure 10. Free-Running Square-Wave Oscillator

The addition of positive feedback ($<10\,\mathrm{mV}$) is also recommended. It is good design practice to ground all unused pins.

Differential input voltages may be larger than supply voltage without damaging the comparator's inputs. Voltages more negative than -0.3 V should not be used.



 $V_{in(min)} \approx 0.4 \text{ V}$ peak for 1% phase distortion ($\Delta\Theta$).

Figure 9. Zero Crossing Detector (Split Supply)

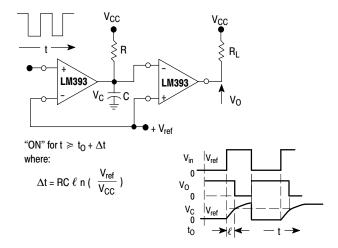


Figure 11. Time Delay Generator

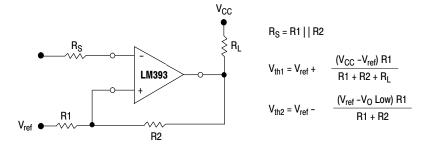
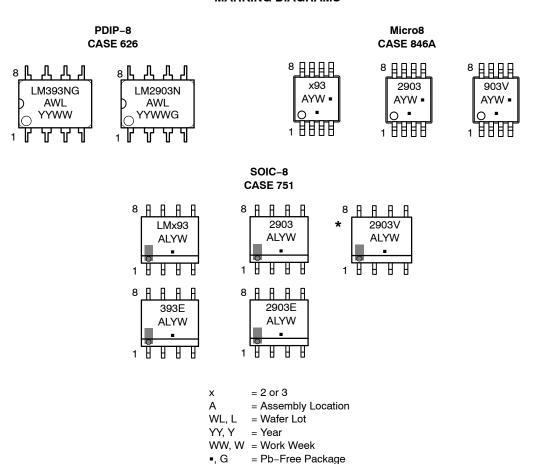


Figure 12. Comparator with Hysteresis

MARKING DIAGRAMS



(Note: Microdot may be in either location)

^{*}This marking diagram also applies to NCV2903DR2G

ORDERING INFORMATION

Device	Operating Temperature Range	Package	Shipping [†]
LM293DG		SOIC-8	98 Units / Rail
LM293DR2G	-25°C to +85°C	(Pb-Free)	2500 / Tape & Reel
LM293DMR2G	20 0 10 100 0	Micro8 (Pb-Free)	4000 / Tape and Reel
LM393DG		SOIC-8	98 Units / Rail
LM393DR2G		(Pb-Free)	2500 / Tape & Reel
LM393EDR2G	0°C to +70°C	SOIC-8 (Pb-Free)	2500 / Tape & Reel
LM393NG	0 0 10 170 0	PDIP-8 (Pb-Free)	50 Units / Rail
LM393DMR2G		Micro8 (Pb-Free)	4000 / Tape and Reel
LM2903DG		SOIC-8	98 Units / Rail
LM2903DR2G		(Pb-Free)	2500 / Tape & Reel
LM2903EDR2G	-40°C to +105°C	SOIC-8 (Pb-Free)	2500 / Tape & Reel
LM2903DMR2G	40 0 10 1100 0	Micro8 (Pb-Free)	4000 / Tape and Reel
LM2903NG		PDIP-8 (Pb-Free)	50 Units / Rail
LM2903VDG		SOIC-8	98 Units / Rail
LM2903VDR2G		(Pb-Free)	2500 / Tape & Reel
LM2903VNG	-40°C to +125°C	PDIP-8 (Pb-Free)	50 Units / Rail
NCV2903DR2G*		SOIC-8 (Pb-Free)	2500 / Tape & Reel
NCV2903DMR2G*		Micro8 (Pb-Free)	4000 / Tape & Reel

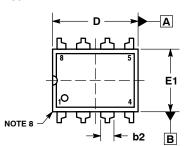
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

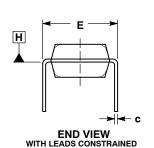


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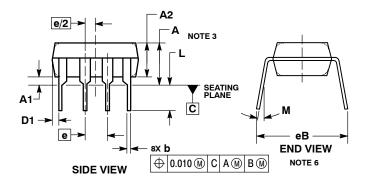
DATE 22 APR 2015



TOP VIEW



NOTE 5



STYLE 1: PIN 1. AC IN 2. DC + IN 3. DC - IN 4. AC IN 5. GROUND 6. OUTPUT

7. AUXILIARY 8. V_{CC}

NOTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: INCHES.
 DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACK-
- AGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
 DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
- DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR
- 6. DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE
- DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
- 8. PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

	INC	HES	MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α		0.210		5.33
A1	0.015		0.38	
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060 TYP		1.52	TYP
С	0.008	0.014	0.20	0.36
D	0.355	0.400	9.02	10.16
D1	0.005		0.13	
Е	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
е	0.100 BSC		2.54	BSC
eВ		0.430		10.92
L	0.115	0.150	2.92	3.81
M		10°		10°

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code = Assembly Location

WL = Wafer Lot YY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

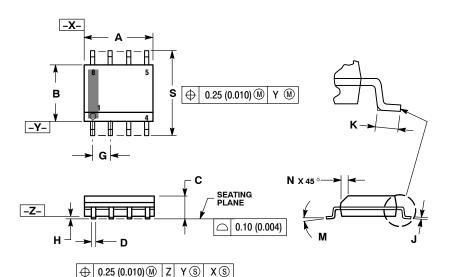
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DATE 16 FEB 2011



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

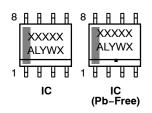
	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27	1.27 BSC		0 BSC
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
М	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location = Wafer Lot

= Year = Work Week = Pb-Free Package XXXXXX AYWW AYWW H \mathbb{H} Discrete **Discrete** (Pb-Free)

XXXXXX = Specific Device Code = Assembly Location Α

= Year ww = Work Week

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	8. DHAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
6. VEE 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	0 COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

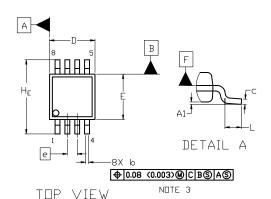
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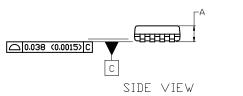
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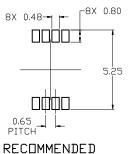






NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION E DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS D AND E ARE DETERMINED AT DATUM F.
- 5. DATUMS A AND B ARE TO BE DETERMINED AT DATUM F.
- 6. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



MOUNTING FOOTPRINT

DIM	MILLIMETERS			
ויונע	MIN.	N□M.	MAX.	
Α			1.10	
A1	0.05	0.08	0.15	
b	0.25	0.33	0.40	
С	0.13	0.18	0.23	
D	2.90	3.00	3.10	
E	2.90	3.00	3.10	
е	0.65 BSC			
HE	4.75	4.90	5.05	
L	0.40	0.55	0.70	

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code A = Assembly Location

Y = Year W = Work Week • = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. SOURCE	PIN 1. SOURCE 1	PIN 1. N-SOURCE
SOURCE	2. GATE 1	2. N-GATE
SOURCE	SOURCE 2	P-SOURCE
GATE	4. GATE 2	4. P-GATE
DRAIN	5. DRAIN 2	5. P-DRAIN
DRAIN	6. DRAIN 2	6. P-DRAIN
7. DRAIN	7. DRAIN 1	7. N-DRAIN
8. DRAIN	8. DRAIN 1	8. N-DRAIN

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